

## IPC020N10L3X1SA1

## IPC020N10L3X1SA1 Information

Heisener.com

**Part Number** IPC020N10L3X1SA1 **Manufacturer** Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 100V SAWN BARE DIE

Package Die

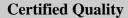
For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com





Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









# IPC020N10L3X1SA1 Specifications

Manufacturer Part NumberIPC020N10L3X1SA1ManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageDieSeriesOptiMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C1A (Tj)Drive Voltage (Max Rds On, Min Rds On)4.5VVgs(th) (Max) @ Id2.1V @ 12µAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds-Vgs (Max)-FET Feature-Power Dissipation (Max)-Rds On (Max) @ Id, Vgs100 mOhm @ 2A, 4.5VOperating Temperature-Mounting TypeSurface MountSupplier Device PackageSawn on foilPackage / CaseDie		
CategoryDiscrete Semiconductor ProductsPackageDieSeriesOptiMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C1A (Tj)Drive Voltage (Max Rds On, Min Rds On)4.5VVgs(th) (Max) @ Id2.1V @ 12μAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds-Vgs (Max)-FET Feature-Power Dissipation (Max)-Rds On (Max) @ Id, Vgs100 mOhm @ 2A, 4.5VOperating Temperature-Mounting TypeSurface MountSupplier Device PackageSawn on foilPackage / CaseDie	Manufacturer Part Number	IPC020N10L3X1SA1
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Package         Die           Series         OptiMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         100V           Current - Continuous Drain (Id) @ 25°C         1A (Tj)           Drive Voltage (Max Rds On, Min Rds On)         4.5V           Vgs(th) (Max) @ Id         2.1V @ 12μA           Gate Charge (Qg) (Max) @ Vgs         -           Input Capacitance (Ciss) (Max) @ Vds         -           Vgs (Max)         -           FET Feature         -           Power Dissipation (Max)         -           Rds On (Max) @ Id, Vgs         100 mOhm @ 2A, 4.5V           Operating Temperature         Surface Mount           Supplier Device Package         Sawn on foil           Package / Case         Die	Category	Discrete Semiconductor Products
Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 1A (Tj) Drive Voltage (Max Rds On, Min Rds On) 4.5V Vgs(th) (Max) @ Id 2.1V @ 12µA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) - FET Feature - Power Dissipation (Max) - Rds On (Max) @ Id, Vgs 100 mOhm @ 2A, 4.5V Operating Temperature Mounting Type Surface Mount Supplier Device Package Sawn on foil Package / Case		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 1A (Tj) Drive Voltage (Max Rds On, Min Rds On) 4.5V Vgs(th) (Max) @ Id 2.1V @ 12µA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) - FET Feature - Power Dissipation (Max) - Rds On (Max) @ Id, Vgs 100 mOhm @ 2A, 4.5V Operating Temperature Mounting Type Surface Mount Supplier Device Package Sawn on foil Package / Case	Package	Die
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 1A (Tj) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) - FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 100 mOhm @ 2A, 4.5V  Operating Temperature  Mounting Type Surface Mount Supplier Device Package Package / Case  MOSFET (Metal Oxide)  100V  100V  100V  14. (Tj)  14. (Tj)  2.1V @ 12μA	Series	OptiMOS?
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C1A (Tj)Drive Voltage (Max Rds On, Min Rds On)4.5VVgs(th) (Max) @ Id2.1V @ 12μAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds-Vgs (Max)-FET Feature-Power Dissipation (Max)-Rds On (Max) @ Id, Vgs100 mOhm @ 2A, 4.5VOperating Temperature-Mounting TypeSurface MountSupplier Device PackageSawn on foilPackage / CaseDie	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5 VVgs(th) (Max) @ Id2.1 V @ 12μAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds-Vgs (Max)-FET Feature-Power Dissipation (Max)-Rds On (Max) @ Id, Vgs100 mOhm @ 2A, 4.5 VOperating Temperature-Mounting TypeSurface MountSupplier Device PackageSawn on foilPackage / CaseDie	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id 2.1V @ 12µA  Gate Charge (Qg) (Max) @ Vgs -  Input Capacitance (Ciss) (Max) @ Vds -  Vgs (Max) -  FET Feature -  Power Dissipation (Max) -  Rds On (Max) @ Id, Vgs 100 mOhm @ 2A, 4.5V  Operating Temperature -  Mounting Type Surface Mount  Supplier Device Package Sawn on foil  Package / Case Die	Current - Continuous Drain (Id) @ 25°C	1A (Tj)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Mounting Type  Surface Mount  Supplier Device Package  Package / Case  Podes	Drive Voltage (Max Rds On, Min Rds On)	4.5V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  - FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  100 mOhm @ 2A, 4.5V  Operating Temperature  - Mounting Type  Surface Mount  Supplier Device Package  Package / Case  Die	Vgs(th) (Max) @ Id	2.1V @ 12μA
Vgs (Max) - CFET Feature Factor	Gate Charge (Qg) (Max) @ Vgs	-
FET Feature - Case - Ca	Input Capacitance (Ciss) (Max) @ Vds	-
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  100 mOhm @ 2A, 4.5V  Operating Temperature  - Mounting Type  Surface Mount  Supplier Device Package  Package / Case  Die	Vgs (Max)	-
Rds On (Max) @ Id, Vgs 100 mOhm @ 2A, 4.5V  Operating Temperature	FET Feature	-
Operating Temperature Mounting Type Surface Mount Supplier Device Package Sawn on foil Package / Case Die	Power Dissipation (Max)	-
Mounting TypeSurface MountSupplier Device PackageSawn on foilPackage / CaseDie	Rds On (Max) @ Id, Vgs	100 mOhm @ 2A, 4.5V
Supplier Device Package Sawn on foil Package / Case Die	Operating Temperature	-
Package / Case Die	Mounting Type	Surface Mount
	Supplier Device Package	Sawn on foil
Report errors?	Package / Case	Die
		Report errors?

#### IPC020N10L3X1SA1 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### IPC020N10L3X1SA1 Payment Methods



















### IPC020N10L3X1SA1 Shipping Methods













If you have any question about IPC020N10L3X1SA1, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com